ROITHNER LASERTECHNIK GmbH
WIEDNER HAUPTSTRASSE 76 1040 VIENNA AUSTRIA
TEL. +43 1 586 52 43 -0, FAX. -44, OFFICE@ROITHNER-LASER.COM

LED570-66-60



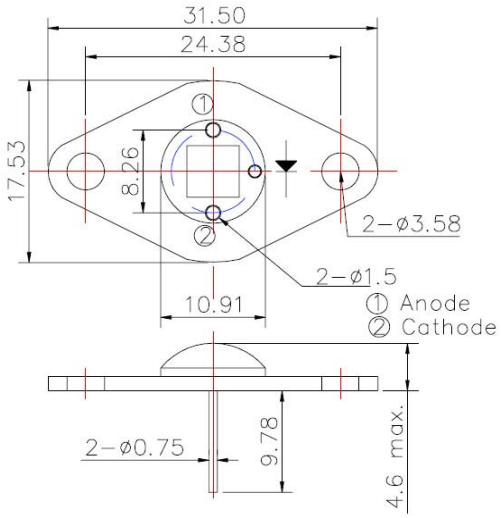
TECHNICAL DATA

High Power LED Array, 60 chips InGaAlP

LED570-66-60 is a wide viewing and extremely high output power illuminator assembled with a total of 60 high efficiency InGaAlP diode chips, mounted on a metal stem TO-66 with AIN ceramics and covered with double coated clear silicone and epoxy resin.
These devices are designed for high current operation with proper heat sinking to improver thermal conductive efficiency.

Specifications

- Structure: InGaAlP, 60 LED chips
- Peak Wavelength: typ. 570 nm
- Optical Output Power: typ. 36 mW
- Package: TO-66 stem with AIN, clear epoxy resin



(Unit: mm)

Absolute Maximum Ratings (T_C=25°C)

Item	Symbol	Value	Unit
Power Dissipation	P_D	4.5	W
Forward Current	I_F	400	mA
Pulsed Forward Current *1	I_{FP}	600	mA
Reverse Voltage	V_R	50	V
Operating Temperature	T_{opr}	-30 … +85	°C
Storage Temperature	T_{stg}	-30 … +110	°C
Soldering Temperature *2	T_{sol}	265	°C

*1 duty = 1%, pulse width = 1 µs
*2 must be completed within 3 seconds



Electro-Optical Characteristics

Item	Symbol	Condition	Min.	Typ.	Max.	Unit
Total Radiated Power	P_O	I_F = 240 mA	-	36	-	mW
Brightness	I_V	I_F = 240 mA	-	7.0	-	cd
Forward Voltage	V_F	I_F = 240 mA	-	11.0	-	V
Reverse Voltage	V_R	I_R = 10 µA	50	-	-	V
Peak Wavelength	λ_P	I_F = 240 mA	560	570	580	nm
Half Width	$\Delta\lambda$	I_F = 240 mA	-	15	-	nm
Viewing Half Angle	$\Theta_{1/2}$	I_F = 240 mA	-	±60	-	deg.

Heat Sink is required, thermal resistance <8K/W

Notes



- This high power LED must be cooled!
- Do not view directly into the emitting area of the LED during operation!
- The above specifications are for reference purpose only and subjected to change without prior notice.